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## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



## LOW DROP POWER SCHOTTKY RECTIFIER

### MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
$V_{RRM}$	30 V
$T_j (max)$	150°C
$V_F (max)$	0.40 V

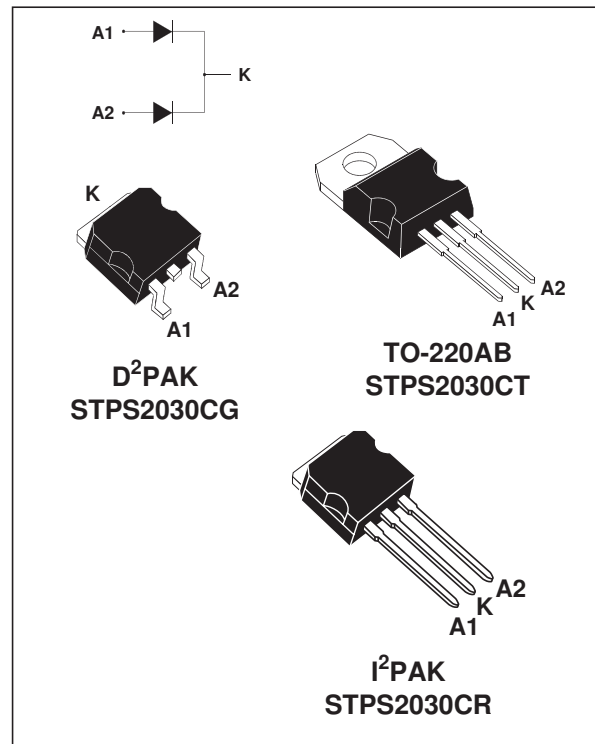
### FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP FOR HIGHER EFFICIENCY
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Dual Schottky rectifier suited for switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-220AB, D<sup>2</sup>PAK and I<sup>2</sup>PAK, this device is intended for use in low voltage high frequency inverters, free wheeling and polarity protection applications.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		30	A
$I_{F(AV)}$	Average forward current	$T_c = 140^\circ\text{C}$ $\delta = 0.5$	Per diode 20 Per device	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	180	A
$I_{RRM}$	Peak repetitive reverse current	$t_p = 2 \mu\text{s}$ square $F = 1\text{kHz}$	1	A
$I_{RSM}$	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$ square	2	A
$P_{ARM}$	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$	3000	W
$T_{stg}$	Storage temperature range		- 65 to + 150	°C
$T_j$	Maximum operating junction temperature *		150	°C
$dV/dt$	Critical rate of rise of reverse voltage (rated $V_R$ , $T_j = 25^\circ\text{C}$ )		10000	V/ $\mu\text{s}$

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case TO-220AB - D <sup>2</sup> PAK - I <sup>2</sup> PAK	Per diode	2.2
		Total	1.3
$R_{th(c)}$	Coupling	0.3	°C/W

**STATIC ELECTRICAL CHARACTERISTICS (per diode)**

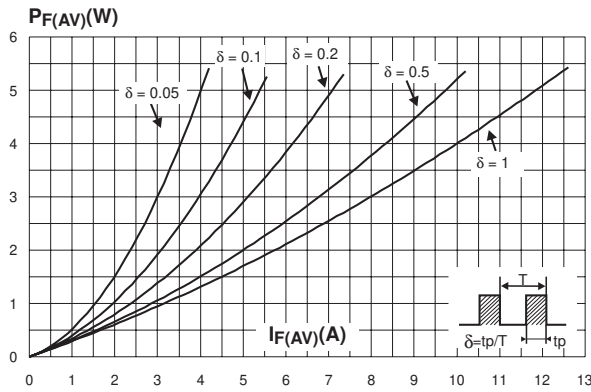
Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit	
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	0.15	1.0	mA	
		$T_j = 125^\circ\text{C}$		80	160		
$V_F^*$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 10\text{ A}$	0.44	0.50	V	
		$T_j = 125^\circ\text{C}$		0.34	0.40		
		$T_j = 25^\circ\text{C}$		$I_F = 20\text{ A}$	0.50		0.58
		$T_j = 125^\circ\text{C}$			0.44		0.52

Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

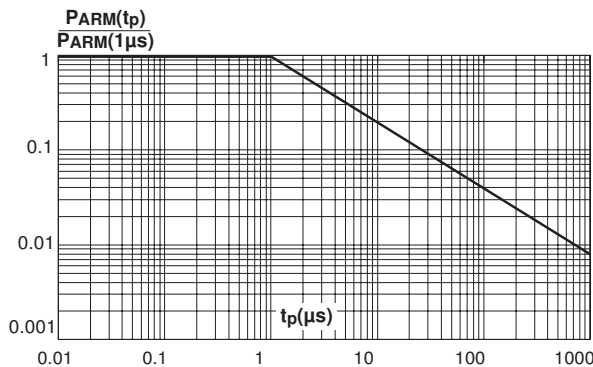
To evaluate the conduction losses use the following equation :

$$P = 0.28 \times I_{F(AV)} + 0.012 I_{F(RMS)}^2$$

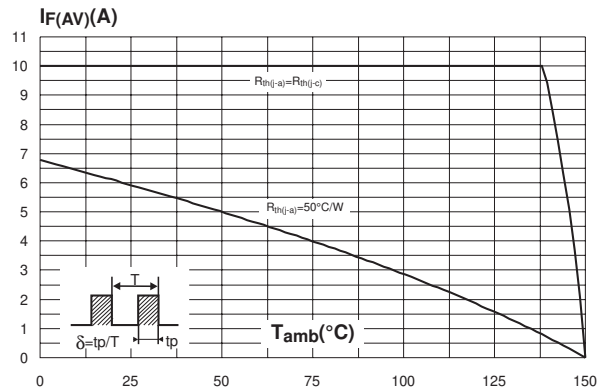
**Fig. 1:** Conduction losses versus average current.



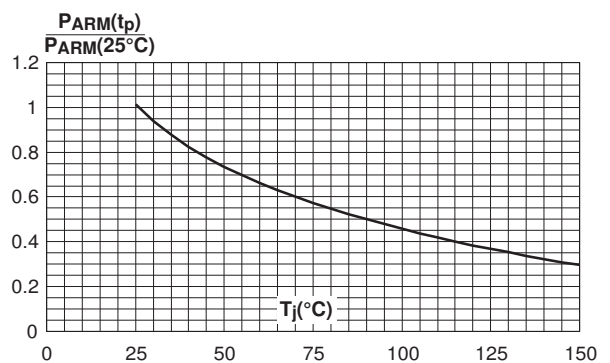
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



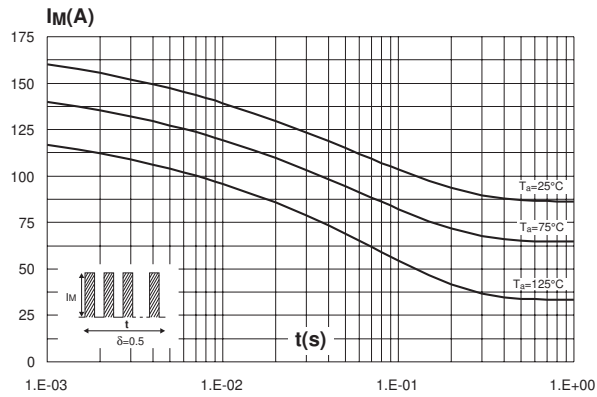
**Fig. 2:** Average forward current versus ambient temperature ( $\delta = 0.5$ ).



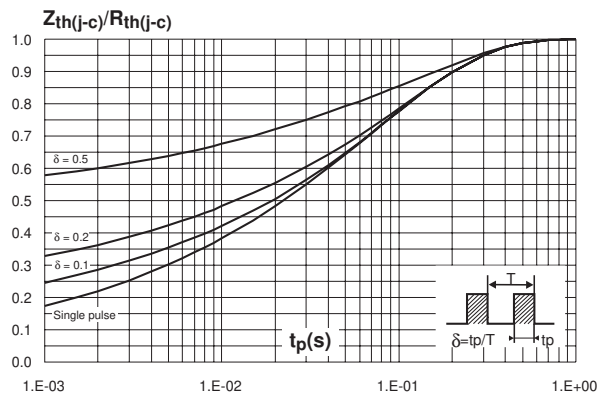
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



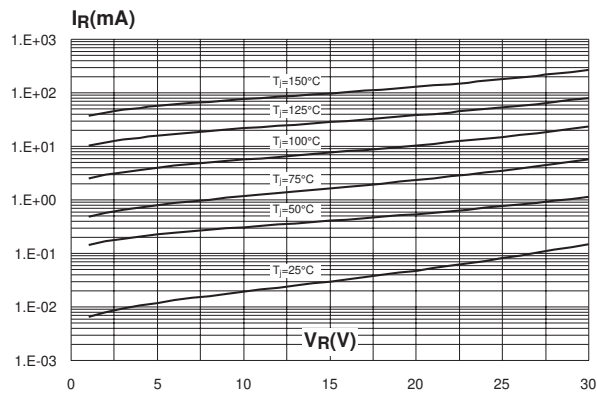
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values).



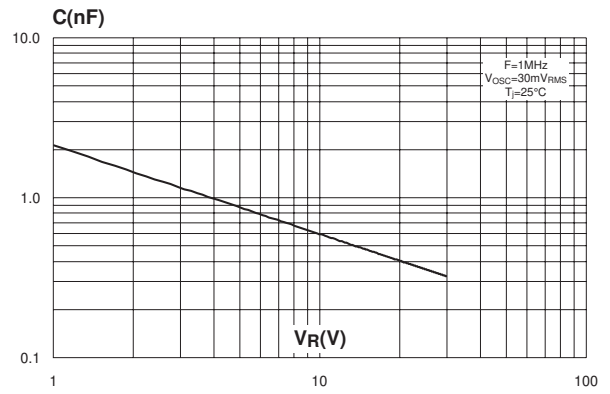
**Fig. 6:** Relative variation of thermal impedance junction to case versus pulse duration.



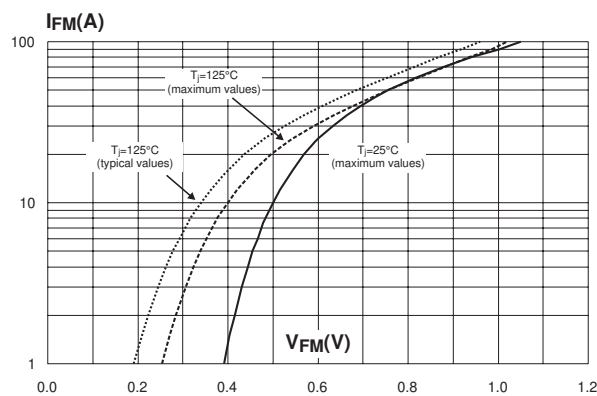
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values).



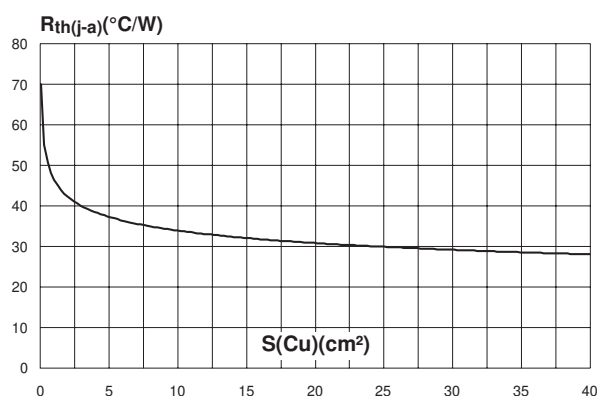
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values).



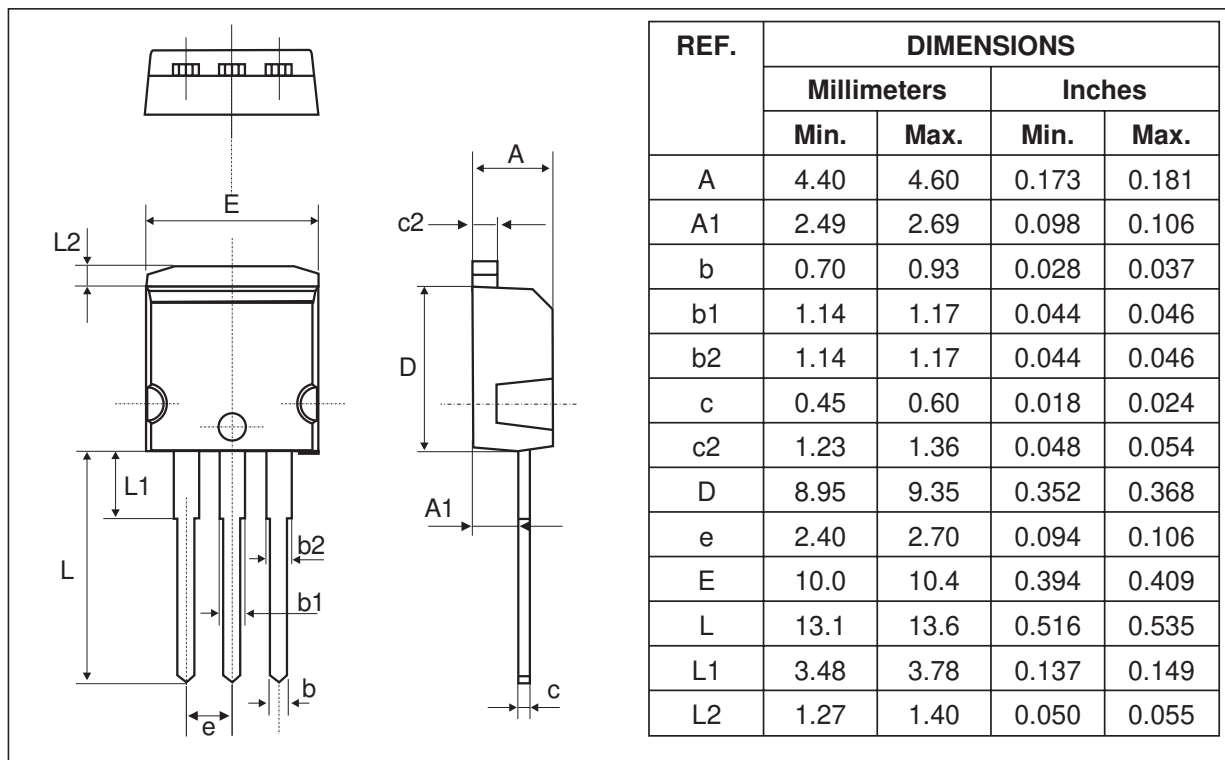
**Fig. 9:** Forward voltage drop versus forward current.



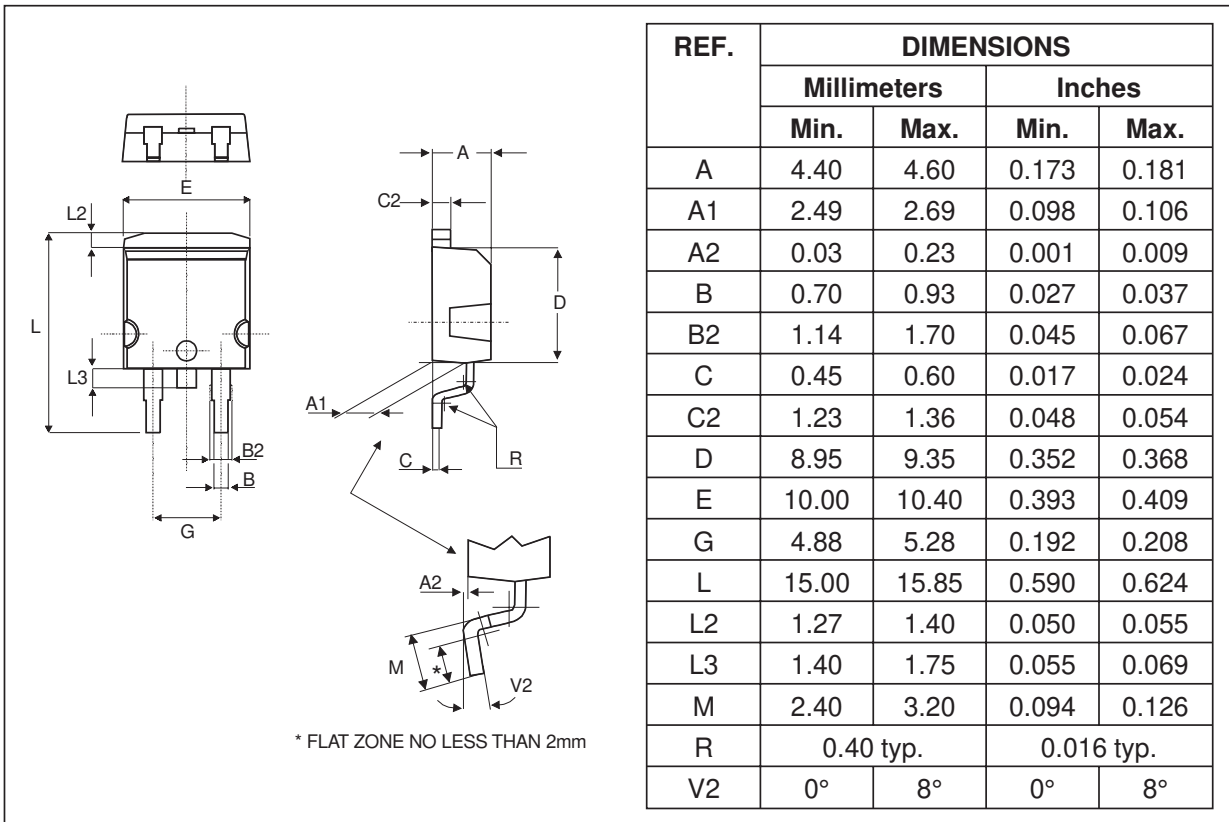
**Fig. 10:** Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu = 35µm).



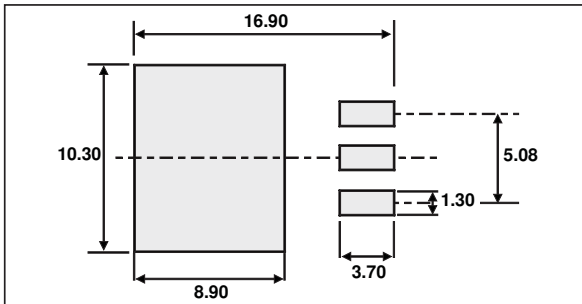
**PACKAGE MECHANICAL DATA**  
I<sup>2</sup>PAK



**PACKAGE MECHANICAL DATA**  
D<sup>2</sup>PAK

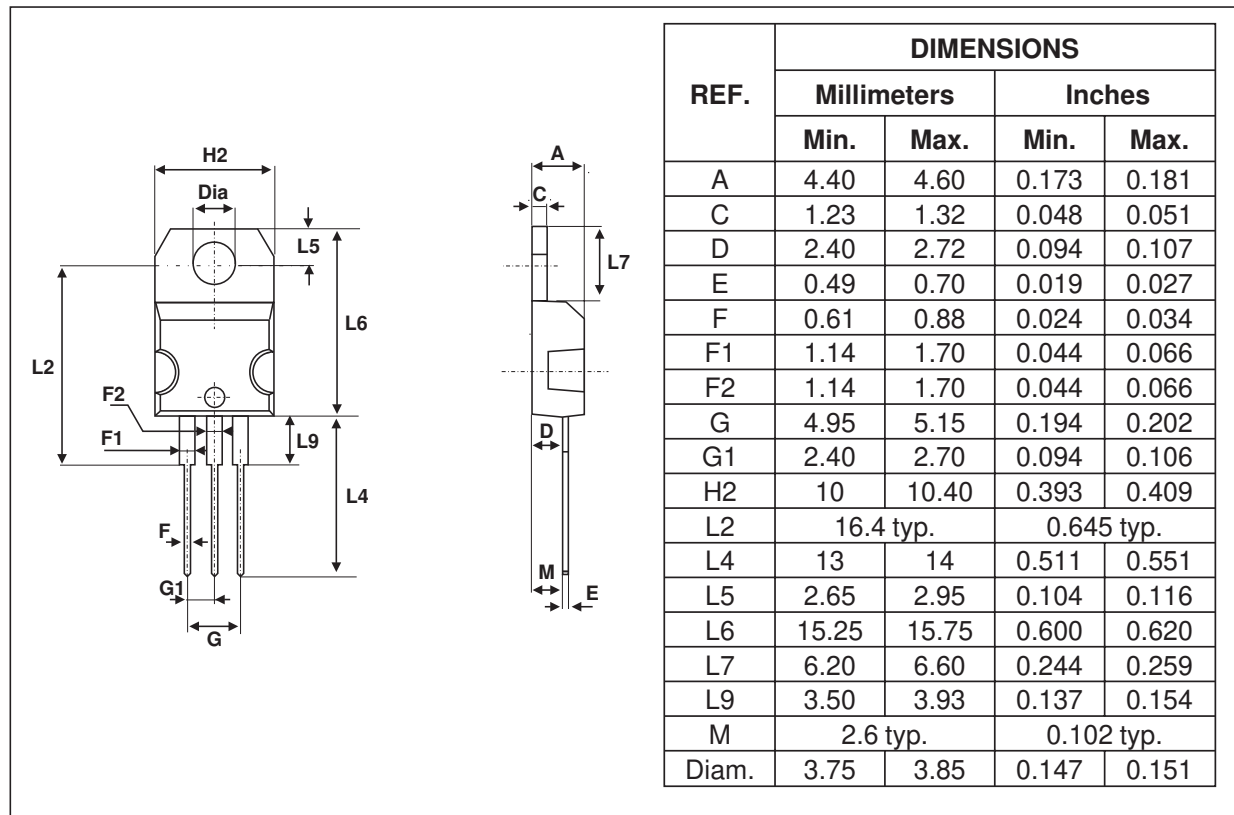


**FOOTPRINT**



# STPS2030CT/CG/CR

## PACKAGE MECHANICAL DATA TO-220AB



- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.55 M.N
- MAXIMUM TORQUE VALUE : 0.70 M.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS2030CT	STPS2030CT	TO-220AB	2.2 g	50	Tube
STPS2030CG	STPS2030CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STPS2030CG-TR	STPS2030CG	D <sup>2</sup> PAK	1.48 g	1000	Tape & reel
STPS2030CR	STPS2030CR	I <sup>2</sup> PAK	1.49 g	50	Tube

- EPOXY MEETS UL94,V0

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